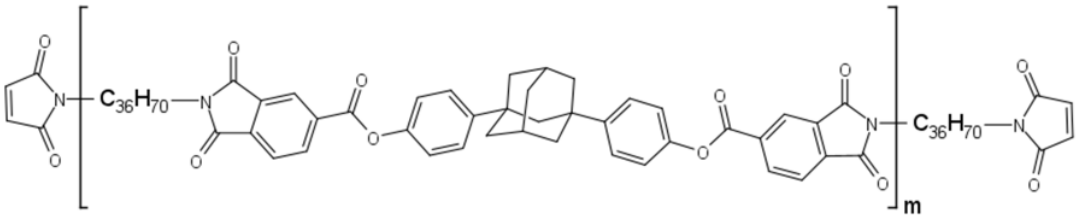
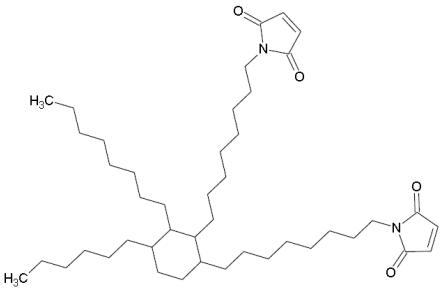
Patent claims

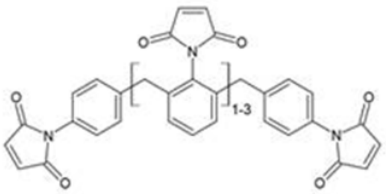
1. A polymerizable mixture comprising a polymerizable compound, a second compound and a third compound, wherein the polymerizable compound has the following structure:



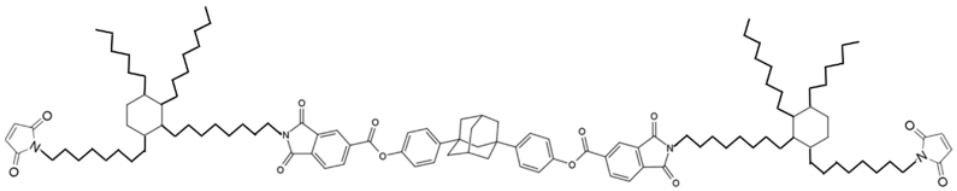
wherein:

m is an integer from 1 to 60;

wherein the second compound is  (BMI-689); and

wherein the third compound is  (Homide 122).

2. The polymerizable mixture according to claim 1, wherein the polymerizable compound is



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3. The polymerizable mixture according to any one of claims 1 to 2, wherein the ratio of the second compound to the third compound is from 10:1 to 1:10, preferably from 1:1 to 1:4.

4. The polymerizable mixture according to any one of claims 1 to 3, wherein the polymerizable compound is present in amount of 5 to 95 wt.-%, preferably 30-50 wt.-% based on the total weight of the mixture.

5. The polymerizable mixture according to any one of claims 1 to 4, wherein the second compound is present in an amount of 0.1 to 50 wt.-%, preferably 0.5 to 5 wt.-% based on the total weight of the mixture.

6. The polymerizable mixture according to any one of claims 1 to 5, wherein the third compound is present in an amount of 0.1 to 50 wt.-%, preferably 0.5 to 10 wt.-% based on the total weight of the mixture.

7. The polymerizable mixture according to any one of claims 1 to 6, wherein the mixture further comprises a curing agent.

8. The polymerizable mixture according to any one of claims 1 to 7, wherein the mixture further comprises as solvent, in particular an organic solvent.

9. A method for forming a dielectric polymer material comprising the following steps:
   a. providing a polymerizable mixture according to any one of claims 1 to 8; and
   b. curing said polymerizable mixture.

10. A dielectric polymer material obtainable by the method according to claim 9.

11. An electronic device comprising a dielectric polymer material according to claim 10.

12. The electronic device according to claim 11, wherein the electronic device is a microelectronic device and the dielectric polymer material is comprised as a repassivation material in a redistribution layer of the microelectronic device.